

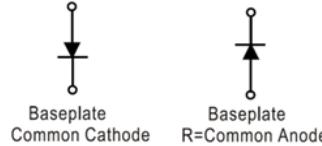
Silicon Power Schottky Diode

V_{RRM} = 150 V - 200 V
I_{F(AV)} = 200 A

Features

- High Surge Capability
- Types from 150 V to 200 V V_{RRM}
- Not ESD Sensitive

D-67 Package



Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

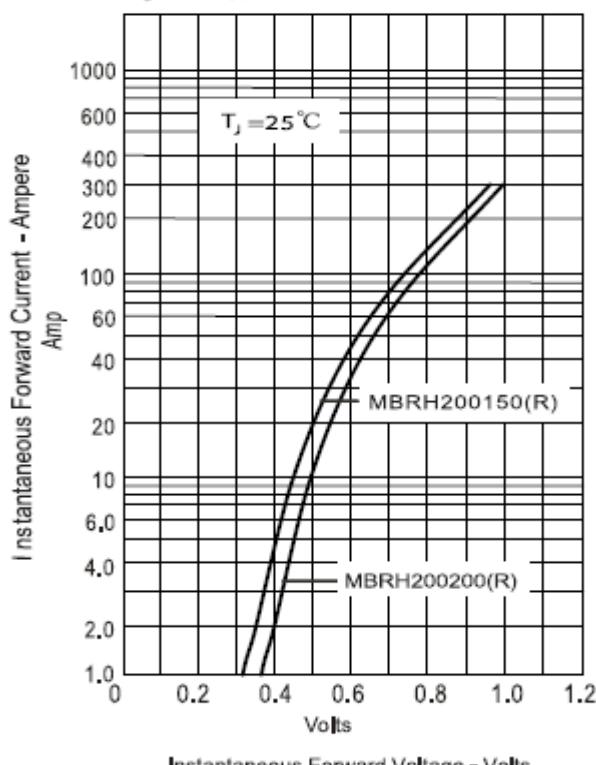
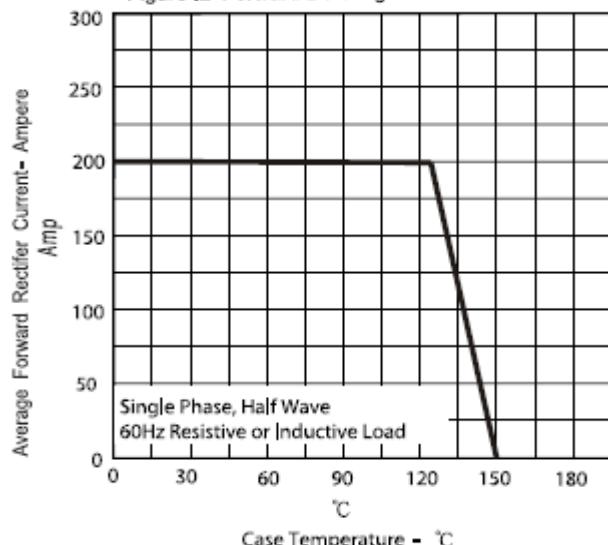
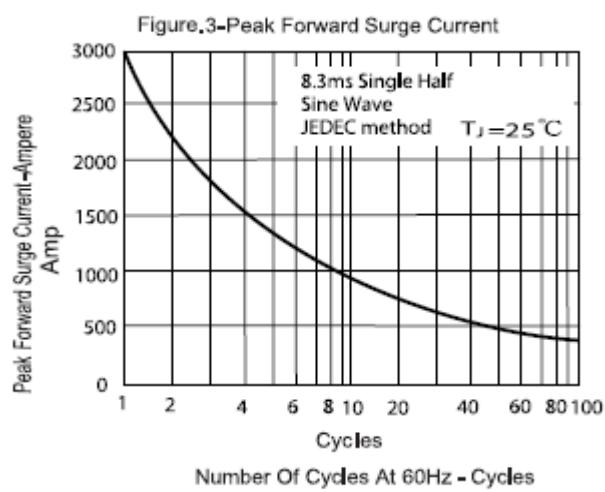
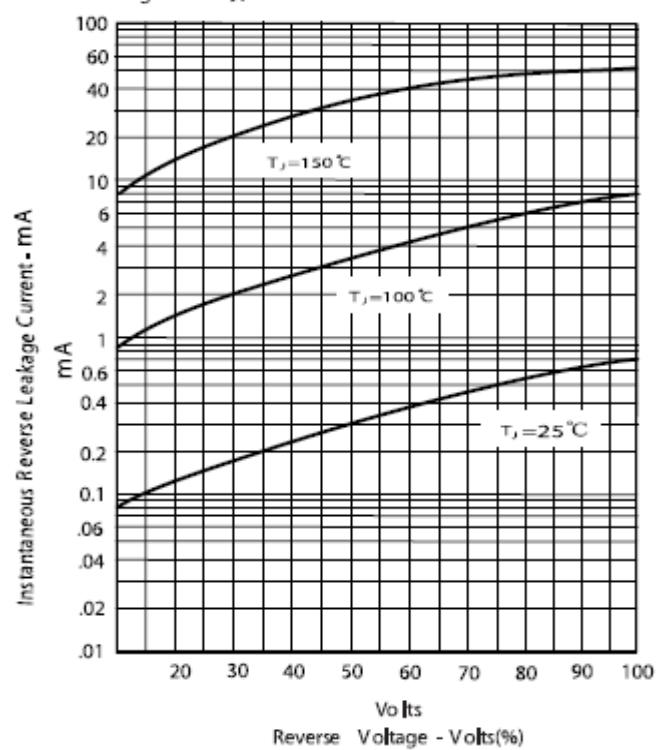
Parameter	Symbol	Conditions	MBRH200150(R)	MBRH200200(R)	Unit
Repetitive peak reverse voltage	V _{RRM}		150	200	V
RMS reverse voltage	V _{RMS}		106	141	V
DC blocking voltage	V _{DC}		150	150	V
Operating temperature	T _j		-55 to 150	-55 to 150	°C
Storage temperature	T _{stg}		-55 to 150	-55 to 150	°C

Electrical characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	MBRH200150(R)	MBRH200200(R)	Unit
Average forward current (per pkg)	I _{F(AV)}	T _C = 125 °C	200	200	A
Peak forward surge current	I _{FSM}	t _p = 8.3 ms, half sine	3000	3000	A
Maximum instantaneous forward voltage	V _F	I _{FM} = 200 A, T _j = 25 °C	0.88	0.92	V
Maximum instantaneous reverse current at rated DC blocking voltage	I _R	T _j = 25 °C T _j = 100 °C T _j = 150 °C	1 10 50	1 10 50	mA

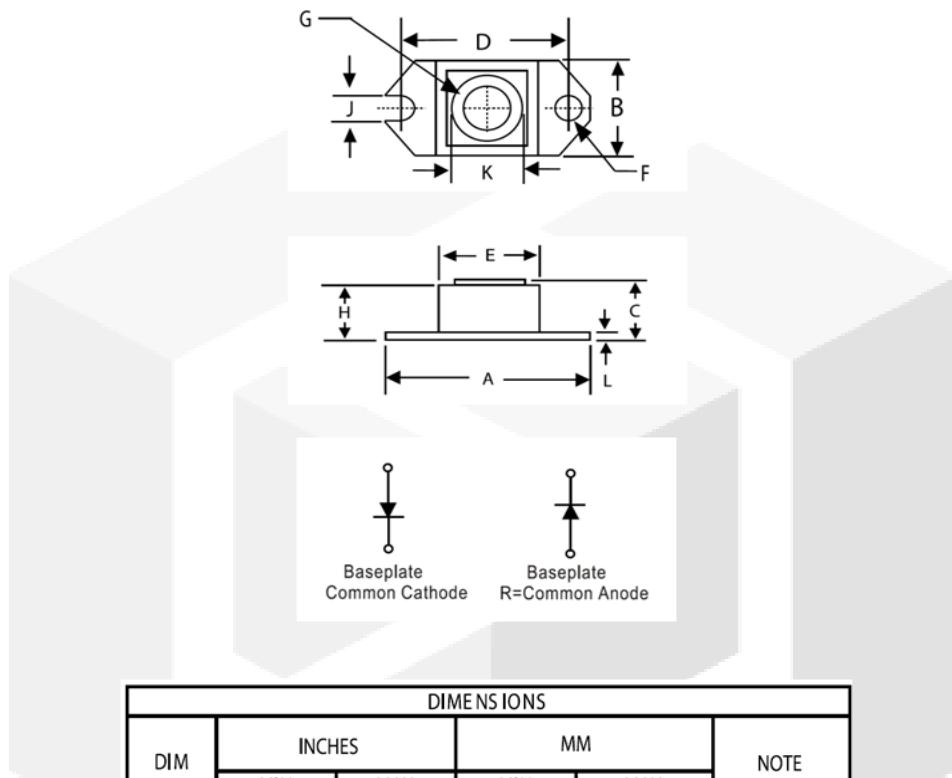
Thermal characteristics

Thermal resistance, junction-case	R _{eJC}	0.35	0.35	°C/W
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Figure .1-Typical Forward Characteristics

Figure .2-Forward Derating Curve

Instantaneous Forward Voltage - Volts

Figure 4-Typical Reverse Characteristics


Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	DIMENSIONS				NOTE	
	INCHES		MM			
	MIN	MAX	MIN	MAX		
A	1.515	1.560	38.48	39.62		
B	.725	.775	18.42	19.69		
C	.595	.625	15.11	15.88		
D	1.182	1.192	30.02	30.28		
E	.736	.744	18.70	18.90		
F	.152	.160	3.86	4.061	Ø	
G	1/4- 20 UNC					
H	.540	.580	13.72	14.73		
J	.156	.160	3.96	4.06		
K	.480	.492	12.20	12.50	Ø	
L	.120	.130	3.05	3.30		